

Light-Harvesting CMOS Power-Supply System for 0–10-mW Wireless Microsensors

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Abstract—Wireless microsensors in consumer products, homes, hospitals, and factories incorporate sensing, processing, and transmission intelligence that can save money, energy, and lives. Although their tiny batteries deplete quickly, harvesting light energy can replenish what they supply. Still, a 1-mm² PV cell can only generate up to 150 μW of the mW's that a wireless microsensor can consume. The battery-assisted light-powered harvester presented here therefore draws 10–130 μW from a 1 × 1-mm² PV cell and assistance from a battery to supply a 10-mW load and recharge the battery with excess PV power. The CMOS system regulates its 1-V output within ±28 mV while supplying 10× more power per 1 mm³ with 94.5% efficiency and 38× with 87.8% efficiency than the best light-harvesting microsystem reported. Unlike others whose efficiencies peak at one power level, efficiency here is 94.5% across v_{PV}'s 10–130-μW and P_{LD}'s 0.5–10-mW with a 18-μH 3 × 3 × 1.5-mm³ inductor and 87.8% with a 22-μH 1.6 × 0.8 × 0.8-mm³ device.

Index Terms—Ambient light, energy harvester, photovoltaic (PV) cell, CMOS microsystem, switched-inductor converter, wireless microsensor, charger, and power supply.

I. LIGHT-HARVESTING MICROSYSTEMS

Advances in the semiconductor industry have made it possible the integration of sensors, processors, memory, and transceivers into tiny wireless devices [1]–[3]. Powering these sensors over extended periods remains a challenge, however, because the tiny on-board batteries that these sensors can fit store little energy. Plus, the cost of personnel employed to replace these batteries is often prohibitive. Luckily, ambient light, motion, heat, and radiation can continually replenish the energy that these batteries supply [4]–[8].

Photovoltaic (PV) cells can generate 150 μW/mm² from sunlight. This is 100× more power than electrostatic or piezoelectric transducers can harvest from motion and thermoelectric generators can generate from heat [4]–[8]. Unfortunately, PV cells output 100× less power with artificial lighting than with sunlight. In other words, mm cells can generate a few μW's indoor and up to 150 μW outdoors.

Although transmissions can require mW's, microsensors seldom transmit in practice. In fact, many sensors mostly idle

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or sense, so on average they often consume nW's [3]. A system can therefore rely on a μW ambient source to replenish the energy that a battery loses to transmissions. For example [7] cites a pulse oximeter sensor node that consumes 90 μW to process and transmit data every 15s. Similarly the intraocular sensor node in [3] consumes 240 nW to measure eye pressure. This way, with the assistance of a battery, an ambient source can supply a wireless microsensor almost indefinitely. The battery supplies on demand what the PV cell avails over time, so light ultimately supplies the system.

The charger-supply system in Fig. 1, for example, harvests PV power P_{PV} from a PV source v_{PV}. When the system idles, v_{PV} can supply more power than the sensor system demands with P_{LD}. The supply system therefore directs excess PV power to the battery v_B. During a transmission, however, P_{PV} may be insufficient, so the system draws assistance from v_B.

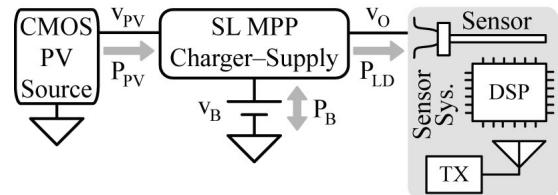


Fig. 1. Light-harvesting wireless microsensor.

The charger-supply [9]–[15] should therefore transfer power from v_{PV} to the output v_O and to v_B and from v_B to v_O. It should do so with minimal losses and at the maximum power point [16]–[18]. Switched inductors are usually more efficient than switched capacitors because switched capacitors typically need more power-consuming switches [8], [19]. This paper therefore proposes a PV-sourced switched-inductor charger-supply system in Sections II–III whose CMOS implementation Section IV describes. Key aspects that distinguish this technology from the state of the art are integration (small size) and energy management (high power-conversion efficiency). Section V discusses how the prototype built compares with the state of the art. Section VI then draws relevant conclusions.

II. CMOS PV-SOURCED CHARGER-SUPPLY

A. CMOS PV Cell

PV cells are essentially PN junctions. In neutral conditions, charge carriers diffuse across the junction, leaving ionized parent atoms behind. So when photons liberate loosely bound electrons in this region, the electric field that these parent atoms establish pull electrons and the holes they leave behind across the region. The net result is a photonic current i_{PH}.

The PN junctions that are normally available in standard CMOS technologies are shallow P⁺ regions in N well, N-well regions over a P substrate, and N⁺ regions over a P substrate. To stack cells over the same substrate, neither terminal can connect to the substrate. This is why only shallow P⁺ regions in an N well like Fig. 2 shows can stack. Unfortunately, these devices incorporate P⁺-N well-P substrate BJTs that leak too much power to the substrate [20]–[21].

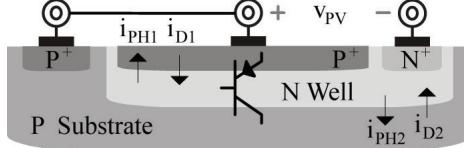


Fig. 2. P⁺ in N well photovoltaic (PV) cell.

Still, this device incorporates two PN junctions with separate depletion regions that together can collect more of the electron–hole pairs that photons liberate. By connecting the junctions in parallel, sunlight can generate more i_{PH} [18]. The diodes that these PN junctions also establish, however, divert some i_{PH} away as i_D . As a result, v_{PV} outputs with i_{PV} the difference $i_{PH} - i_D$.

The power that i_{PH} generates P_{PH} and the power that i_D consumes P_D both hinge on v_{PV} . So PV power P_{PV} in Fig. 3 rises with v_{PV} until P_D 's incremental loss $-\Delta P_D$ cancels P_{PH} 's gain $+\Delta P_{PH}$. The maximum power point P_{MPP} happens when these incremental variations balance and increases with light intensity. The v_{PV} that outputs P_{MPP} can be 400–500 mV.

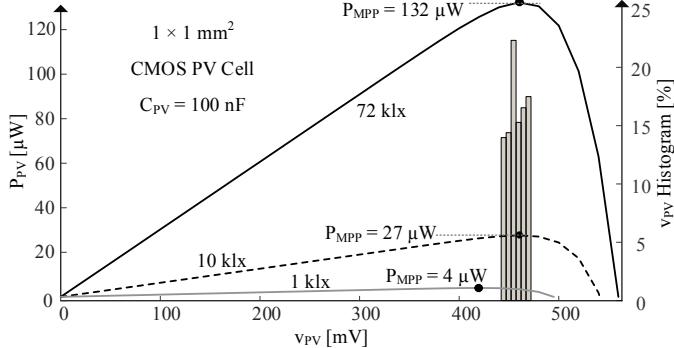


Fig. 3. Measured photovoltaic power and histogram in the system.

B. Power Stage

The power stage should draw power from the PV cell v_{PV} to feed the sensor system at v_O . Excess PV power should replenish the battery v_B . When PV power cannot sustain the sensor, the system should draw assistance from v_B . In other words, the power stage proposed draws power from v_{PV} and v_B and supplies v_O and v_B , depending on operating conditions.

Although the sensor system consumes less power with a lower supply voltage v_O , the supply system and other analog electronics stop working below a headroom level that is often about 1 V [3]. Breakdown voltage, which in this case is 1.8 V, is another limit that constrains v_B . So the power stage proposed in Fig. 4 boosts v_{PV} 's 350–500 mV to v_O 's 1 V and v_B 's 1.8 V and bucks v_B 's 1.8 V to v_O 's 1 V.

Unfortunately, on-chip inductors usually suffer from low inductance L_X and high resistance R_L . This is a double challenge because low L_X holds less energy with a given

current i_L . So i_L is usually high, and with a high R_L , ohmic power is that much higher. A higher switching frequency f_{SW} can keep i_L from reaching such a high level. The problem with this is that controlling and switching the network at higher f_{SW} requires more power. Luckily, commercially available off-chip inductors with sL_X-to-R_L ratios (i.e., quality factors) of 50–100 can be as small as 1 mm³ [13]. But since they are still bulky, the system in Fig. 4 proposes to use only one inductor.

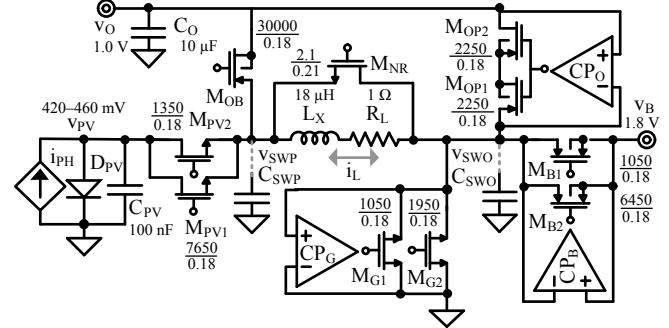


Fig. 4. CMOS PV-sourced charger-supply stage.

Inductors energize with positive voltages and drain with negative voltages. So with transistors M_{PV1} and M_{PV2} closed, M_{G1} in Fig. 4 and Fig. 5 closes to magnetize L_X from v_{PV} . M_{G1} then opens and M_{OP1} – M_{OP2} closes to apply the negative voltage that drains L_X into v_O . If the load does not need energy, M_{B1} closes instead to drain L_X into v_B . But if the load still needs energy after draining L_X into v_O , M_{PV1} – M_{PV2} opens and M_{OB} closes. With M_{OB} closed, M_{B1} – M_{B2} then closes to energize L_X from v_B into v_O and M_{G1} – M_{G2} later close to drain L_X into v_O . M_{G1} – M_{G2} 's and M_{B1} – M_{B2} 's source terminals swap positions because current can flow in both directions.

MOSFETs burn ohmic power P_{MR} and require gate-drive power P_{MG} to switch. Since P_{MR} and P_{MG} both climb with longer channels, channel lengths in Fig. 2 are the shortest possible that can sustain 1.8 V. On the other hand, P_{MR} falls and P_{MG} rises with wider channels. So overall losses fall with wider transistors until the rise in P_{MG} cancels the fall in P_{MR} . In other words, transistors consume the least power when their channels are optimally wide for the current they conduct.

This is why some transistors in Fig. 4 are in parallel. For example, M_{B1} alone closes to drain L_X into v_B the energy that v_{PV} supplies and M_{B1} and M_{B2} together close to energize L_X from v_B because v_B delivers more power than v_{PV} . M_{G1} alone closes to energize L_X from v_{PV} and M_{G1} and M_{G2} together close to drain L_X into v_O the energy that v_B supplies for the same reason. M_{PV2} is optimally sized to deliver PV power P_{PV} . But since v_{PV} is always connected to L_X when the system is over-sourced, M_{PV2} does not require P_{MG} . So paralleling M_{PV1} in this mode reduces resistance without sacrificing P_{MG} .

M_{OP1} and M_{OP2} are in series so their body diodes block one another. This way, body diodes cannot conduct current when the combined switch is off. With only one transistor, the bulk would connect to v_O to keep the body diode from engaging when the switching node v_{SWO} falls. This, however, keeps v_{SWO} from climbing above v_O to v_B when directing i_L to v_B .

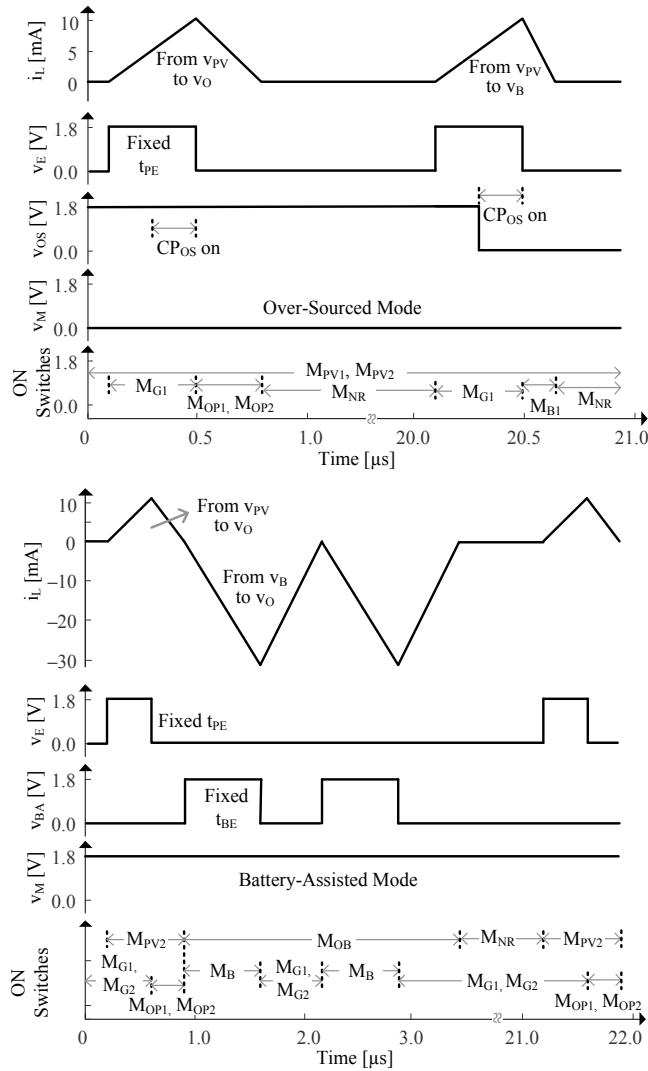


Fig. 5. Timing diagram (a) over-sourced (b) battery-assisted.

To remain at the maximum power point P_{MPP} in Fig. 3, v_{PV} should be steady. Similarly, v_O should be steady for the wireless microsensor to operate optimally and reliably. The supply system, however, switches L_X between input and output terminals, so the current pulled from v_{PV} and steered into v_O change abruptly from zero to i_L . The purpose of capacitors C_{PV} and C_O is to reduce the voltage fluctuations that these abrupt current changes produce.

Between transfers, remnant energy in L_X drains into parasitic switch-node capacitances C_{SWP} and C_{SWO} and cycle back to L_X in resonant fashion. L_X and C_{SW} 's exchange energy back and forth until resistances burn the energy. The purpose of M_{NR} is to burn this energy quickly so the oscillations and noise that L_X and C_{SW} 's would otherwise produce fade faster.

The controller decides which transistors to close. The controller also determines which energizing switches to open. Draining output switches, however, can open like diodes, when they stop receiving L_X 's current i_L . For this, comparators CP_B , CP_O , and CP_G open M_{B1} , $M_{OPI1}-M_{OPI2}$, and $M_{G1}-M_{G2}$ when v_{SWO} falls below v_B or v_O or v_{SWO} rises above ground. To save power, these comparators activate after the controller closes the switches and power off after the comparators open

them. CP_G , CP_B , and CP_O are trimmed so their offsets and delays balance to keep efficiency from suffering. Since M_{G1} is also an energizing switch when drawing PV power P_{PV} , the controller opens M_{G2} when M_{G1} energizes.

III. CMOS CONTROLLER

The controller proposed in Fig. 6 draws enough power from the PV cell to keep v_{PV} near the maximum power point peak v_{MPP} . It also steers enough of that power, and if necessary, additional power from the battery v_B to keep v_O near its 1-V target v_R . In other words, the controller regulates v_{PV} and v_O . v_{PV} is programmable with v_{MPP} and v_O with v_R .

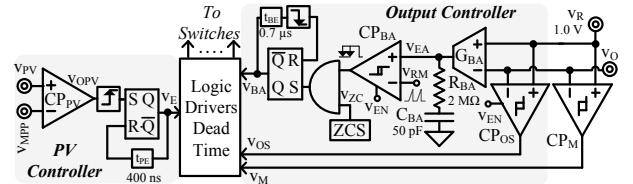


Fig. 6. CMOS controller.

The controller decomposes into four sections: PV, output, mode, and logic control. When gate signals to the transistors that connect to v_{SWP} and v_{SWO} in Fig. 4 crisscross, switches close and the supply nodes to which they connect short-circuit. This is a problem that the logic avoids by inserting dead time between the gate signals of adjacent switches. The logic also includes drivers large enough and quick enough to drive the large capacitive gates that power transistors present.

The controller consumes quiescent power P_Q that climbs with switching frequency f_{SW} . To limit this loss, f_{SW} should be low. Except, energizing and draining L_X across long periods delivers more power than the sensor system requires. So the charger-supply here draws and delivers infrequent energy packets that are large enough to sustain the system. In other words, L_X conducts discontinuously.

This way, the switching network excludes the inductor pole and out-of-phase right-half-plane zero that boosting switched inductors normally exhibit [22]–[23]. This is important because, in the absence of other poles and zeros, C_{PV} and C_O establish the only dominant poles in the loops that the PV and output controllers close. As a result, their respective loop gains reach 0 dB with 90° of phase margin, so the loops are stable.

A. Photovoltaic Regulation

When open-circuited, the PV cell's photonic current i_{PH} in Fig. 4 feeds parasitic diode D_{PV} until v_{PV} reaches 500–600 mV. At this level, i_{PV} , and in consequence, P_{PV} are zero. The purpose of the PV controller in Fig. 6 is to draw enough power from v_{PV} to keep v_{PV} at the level that i_{PV} with v_{PV} output the highest power P_{MPP} . In steady state, v_{PV} should be 350–500 mV [18].

Since transistors consume the least power when they conduct a particular current, the system draws PV energy packets E_{PV} 's that always peak to the same level. For this, L_X energizes across the 400 ns that the fixed-pulse block t_{PE} in Fig. 6 sets. M_{PV1} , M_{G1} , M_{B1} , and $M_{OPI1}-M_{OPI2}$ in Fig. 4 are optimally sized to conduct this energy. The controller adjusts P_{PV} by adjusting the frequency f_{PV} of the packets.

For this, comparator CP_{PV} commands L_X to draw an E_{PV} when v_{PV} surpasses its targeted maximum power-point peak v_{MPP} . Drawing E_{PV} (at 20 ms in Fig. 7) pulls v_{PV} below v_{MPP} . Excess i_{PH} then charges C_{PV} until v_{PV} again surpasses v_{MPP} , at which point CP_{PV} prompts L_X to draw another packet that discharges C_{PV} . v_{PV} rises and falls this way about its optimal average level $v_{PV(AVG)}$. Although this rippling behavior shifts v_{PV} from its absolute optimal setting, like the histogram in Fig. 3 shows, C_{PV} limits the variation to such a degree that P_{PV} is still within 1% of P_{MPP} .

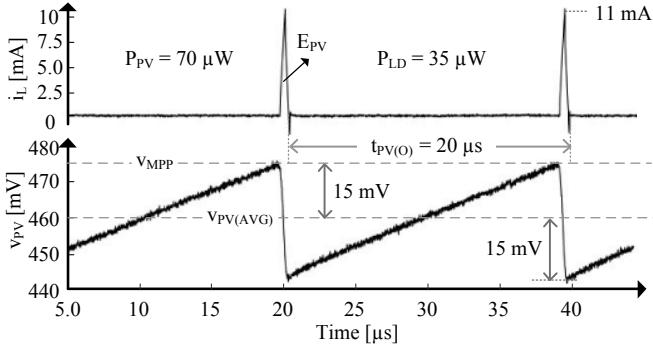


Fig. 7. Measured inductor current and photovoltaic voltage.

Operationally, CP_{PV} sets a flip-flop whose output commands the logic to energize L_X across the 400 ns that t_{PE} sets. v_{MPP} is the output of a lookup table that determines which setting is optimal for the light intensity received. The advantage of the look-up table over open-circuiting the PV cell to sense the cell's state is that the latter cannot output power across the open-circuit interruption. The look-up table that generates v_{MPP} is set externally. The look-up table that sets v_{MPP} adjusts v_{PV} so the PV cell remains at the maximum power point, irrespective of process and operating conditions. Since i_{PH} is higher for more intense light and a higher i_{PH} can supply a larger E_{PV} , i_{PH} and E_{PV} charge and discharge C_{PV} faster. In other words, packet frequency f_{PV} in Fig. 8 is proportional to the PV power that light intensity establishes.

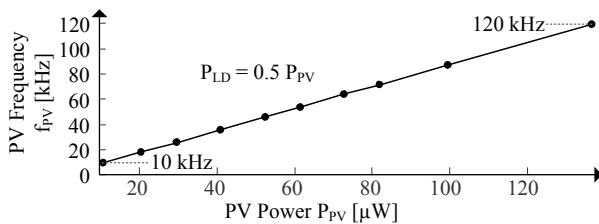


Fig. 8. Measured PV packet frequency.

B. Output Regulation

Over-Sourced: When PV power P_{PV} surpasses the needs of the sensor system, comparator CP_{OS} determines when to steer excess power to the battery v_B . For this, CP_{OS} compares the output v_O with the targeted 1-V reference v_R . So as long as the load pulls v_O below v_R , CP_{OS} commands the logic, switches, and L_X to draw and steer PV energy packets E_{PV} 's (at 15 ms in Fig. 9) to v_O . CP_{OS} prompts L_X to direct excess E_{PV} 's to v_B (at 30 ms in Fig. 9) when v_O rises above v_R .

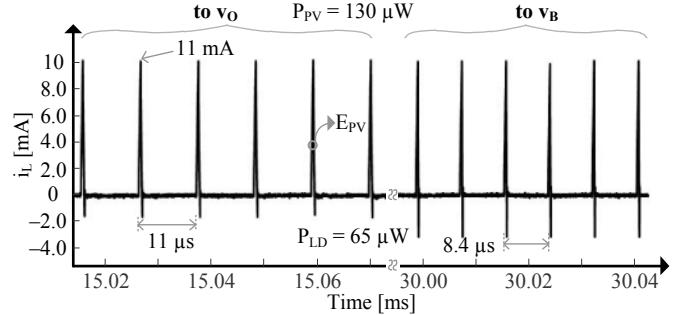


Fig. 9. Measured over-sourced inductor current.

Since v_O 's 1 V is lower than v_B 's 1.8 V, L_X drains more slowly with v_O than with v_B . So although the PV controller's fixed-pulse block t_{PE} always energizes L_X across the same 400 ns to 11 mA, L_X 's i_L falls more slowly when directed to v_O (at 15 ms). Interestingly, v_{PV} delivers more power to v_O this way because L_X drains into v_O while still connected to v_{PV} . But since the P_{MPP} that light intensity sets does not change, the PV controller delivers packets to v_O less often. This is why v_O in Fig. 9 receives E_{PV} 's every 11 μs and v_B every 8.4 μs.

To keep noise from inadvertently tripping the comparator, CP_{OS} incorporates hysteresis. This means that v_O does not stop receiving E_{PV} 's until v_O in Fig. 10 falls 28 mV below v_R 's 1 V. Similarly, but in the opposite direction, v_O does not begin to receive E_{PV} 's until v_O climbs 28 mV above v_R 's 1 V. To save power, CP_{OS} only activates when the system is over-sourced, and only while energizing L_X . Hysteresis is built into CP_{OS} and designed to be higher than 20 mV to suppress the effects of ± 5 m-V noise when tolerance is up to $\pm 50\%$.

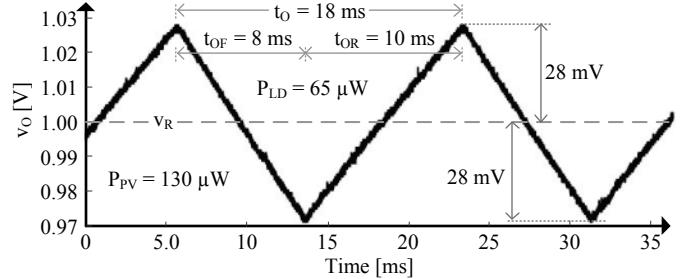


Fig. 10. Measured over-sourced output voltage.

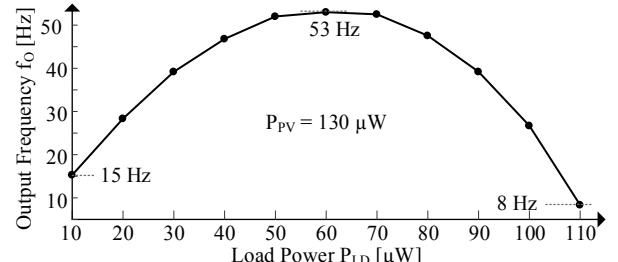


Fig. 11. Measured output frequency.

C_O 's charge and discharge times t_{OR} and t_{OF} set v_O 's output frequency f_O . The system load P_{LD} discharges C_O (between 6 and 14 ms in Fig. 10) because L_X disconnects from v_O when directing E_{PV} 's to v_B . When receiving E_{PV} 's, however, excess PV power charges C_O (between 14 and 24 ms). Since this excess energy is greater with lighter loads and *vice versa*, t_{OR} and t_{OF} shift in opposite directions with P_{LD} . In Fig. 11, for example, t_{OR} and t_{OF} balance and f_O peaks at 53 Hz when P_{LD}

is 60 μW . Lighter loads extend t_{OF} more than excess PV power shortens t_{OR} , so f_0 falls to 15 Hz with 10 μW . Heavier loads, on the other hand, shorten t_{OF} less than excess power lengthens t_{OR} , so f_0 similarly falls to 8 Hz with 110 μW .

Battery-Assisted: When PV power P_{PV} is not enough to feed the sensor system, the logic automatically delivers v_{PV} 's energy packet E_{PV} to v_O and another packet E_B from v_B . Transconductor G_{BA} closes the feedback loop that determines how much additional power v_B delivers.

Since transistors consume the least power when they conduct a particular current, the system draws energy packets that peak to the same level. For this, L_X energizes across the time that the fixed-pulse block t_{BE} in Fig. 6 sets. Since the load can pull up to 10 mW and the PV cell can only supply up to 130 μW , v_B must be able to supply more power than v_{PV} . This is why t_{BE} is 300 ns longer than t_{PE} , so L_X can peak to 31 mA in Fig. 12, and with 31 mA, deliver a larger energy packet E_B . $M_{\text{B}1}$ and $M_{\text{B}2}$, $M_{\text{G}1}$ and $M_{\text{G}2}$, and M_{OB} in Fig. 4 are optimally sized for this energy level. The controller adjusts P_B by adjusting the number of packets delivered between E_{PV} 's.

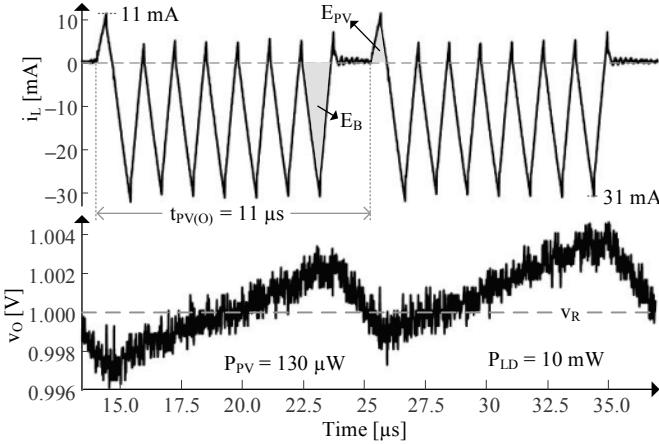


Fig. 12. Measured battery-assisted inductor current and output voltage.

For this, G_{BA} senses and amplifies the error v_{EA} between v_O and the targeted v_R . CP_{BA} then compares v_{EA} to v_{RM} 's sawtooth ramp to determine how long the system should deliver E_B 's. When v_O falls below v_R , for example, v_{EA} rises and CP_{BA} waits longer for v_{RM} to reach this higher v_{EA} . In the interim, the zero-current sensor ZCS, which resets after every E_B , continues to set the flip-flop that triggers new E_B 's. The system delivers consecutive E_B 's this way until CP_{BA} trips.

To save power, G_{BA} activates only when the system enters battery-assisted mode. CP_{BA} is on only while delivering E_B 's. More specifically, CP_{BA} activates after L_X sends E_{PV} and powers off after L_X sends the last E_B .

To avoid conflicting L_X commands from the PV and output controllers, the logic inserts a 1.5- μs blank time before every E_{PV} . This way, E_B 's and E_{PV} 's never overlap. Incidentally, since E_{PV} is not high enough to supply the load, C_0 does not begin to charge until L_X delivers the first E_B . This is why v_O in Fig. 12 only rises when receiving E_B 's.

When an integer number of E_B 's across one t_{PV} does not match the steady-state needs of the system, the system oversupplies and undersupplies E_B 's in alternate t_{PV} cycles so the average number of E_B 's is the fraction that matches the

load. In Fig. 13, for example, the system delivers two sets of 7 E_B 's between every set of 6, which is 6.67 E_B 's on average. This variation in E_B 's produces the subtle sub-harmonic fluctuation seen in v_O in Figs. 11 and 12.

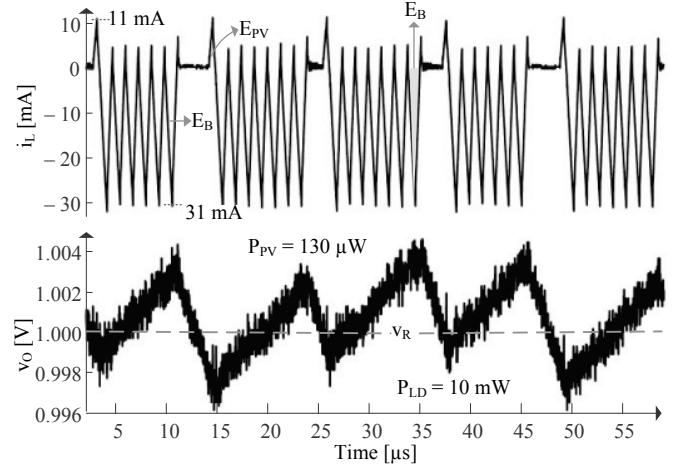


Fig. 13. Measured output when alternating the number of battery packets.

Without R_{BA} and C_{BA} , G_{BA} 's high output resistance sets a low-frequency pole p_{EA} that along with C_0 's pole p_0 can reduce the loop gain to 0 dB with 0° of phase margin. Although C_{BA} pulls p_{EA} to lower frequency, R_{BA} current-limits C_{BA} 's current to remove the effects of the dominant pole:

$$p_{\text{EA}} = \frac{1}{2\pi(R_{\text{EA}} + R_{\text{BA}})C_{\text{BA}}}, \quad (1)$$

with a zero:

$$z_{\text{BA}} = \frac{1}{2\pi R_{\text{BA}} C_{\text{BA}}}. \quad (2)$$

R_{BA} 's then establishes a pole p_{BA} with v_{EA} 's parasitic capacitance C_{EA} that is greater than the 0-dB frequency $f_{0\text{dB}}$ that p_0 (without the effects of p_{EA}) sets. The output load R_O and effective inductor impedance R_L along with C_0 sets the output pole:

$$p_0 = \frac{1}{2\pi(R_L || R_O)C_0}. \quad (3)$$

In other words, z_{BA} cancels p_{EA} and p_{BA} is higher than $f_{0\text{dB}}$, so the system is stable.

C. Mode Regulation

Comparator CP_M in Fig. 6 ultimately determines whether battery assistance is needed or not. In other words, CP_M determines which mode of operation the system should adopt. For this, CP_M compares v_O to its targeted v_R and incorporates hysteresis whose threshold limits are well above and well below the v_O peaks that CP_{OS} and G_{BA} produce when they regulate v_O . So if E_{PV} 's alone (when CP_{OS} regulates v_O) cannot sustain the load P_{LD} , excess P_{LD} discharges C_0 from cycle to cycle. When v_O reaches CP_M 's lower threshold, CP_M trips high into battery-assisted mode. Similarly, if one E_B (when G_{BA} regulates v_O) oversupplies P_{LD} , excess P_B charges C_0 to CP_M 's upper threshold, where CP_M trips low into over-sourced mode.

Static and dynamic components ultimately dictate CP_M 's hysteretic limits. Because when v_O reaches CP_M 's lower static threshold, the system does not respond until a propagation

delay later. As a result, v_O rises or falls an additional amount. This dynamic effect diminishes, however, with slow variations in v_O . When load power P_{LD} in Fig. 14 suddenly falls from 5 mW to 50 μ W, for example, excess battery power P_B charges C_O slowly until v_O reaches CP_M 's upper 60-mV threshold. When P_{LD} suddenly rises back to 5 mW, however, excess P_{LD} discharges v_O so quickly that the system does not react until after v_O falls below the 60-mV threshold by another 12 mV.

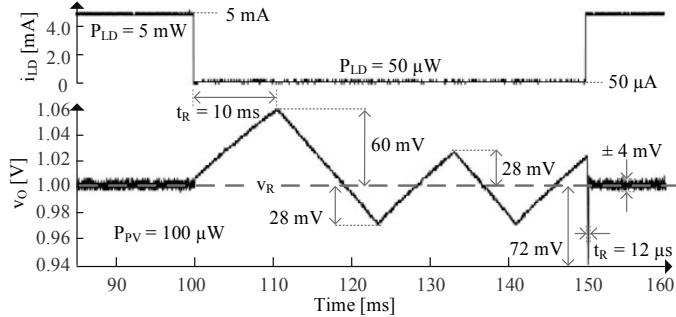


Fig. 14. Measured output when subjected to mode-swinging load dumps.

IV. PROTOTYPE IMPLEMENTATION

The $1 \times 1\text{-mm}^2$ and $0.9 \times 0.9\text{-mm}^2$ CMOS dies in Fig. 15 integrate the PV cell, power transistors, and controller blocks in Figs. 2, 4, and 5. Test circuits and power passives L_X , C_{PV} , and C_O in Fig. 4 are off-chip on the two-layer board shown. L_X is either 18 μ H with 1 Ω of dc resistance and $3 \times 3 \times 1.5\text{ mm}^3$ in volume or 22 μ H with 2 Ω and $1.6 \times 0.8 \times 0.8\text{ mm}^3$. Although the former occupies more space, its resistance burns less power. C_{PV} is 100 nF and occupies $1.0 \times 0.5 \times 0.5\text{ mm}^3$ and C_O is 10 μ F and occupies $1.6 \times 0.8 \times 0.8\text{ mm}^3$.

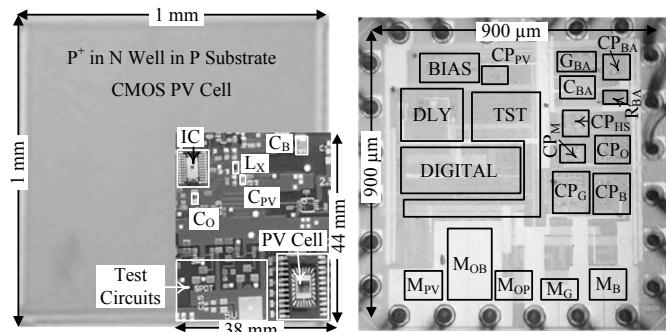


Fig. 15. PV-cell and charger-supply dies and test board.

A. PV Power

The P^+ in N well on P substrate PV cell outputs up to 4, 27, and 131 μ W with 1, 10, and 72 klx of light intensity like Fig. 3 shows. These maximum levels result when v_{PV} is 420, 460, and 460 mV. But since L_X draws discrete energy packets, v_{PV} ripples about this optimum point. So like the histogram in Fig. 3 and waveform in Fig. 7 illustrate, v_{PV} ripples from 442 to 476 mV with 72 klx. This small variation keeps P_{PV} within 1% of P_{MPP} in Fig. 3. The frequency of PV packets f_{PV} is 10–120 kHz when P_{PV} is 10–130 μ W. Note that reducing C_{PV} increases v_{PV} 's ripple, which increases P_{PV} 's deviation from P_{MPP} . In other words, a lower C_{PV} reduces P_{PV} . But since sensitivity near P_{MPP} is low, a higher C_{PV} has little effect.

B. Output Regulation

L_X delivers 11-mA packets from the PV cell in Figs. 6 and 10 and 31-mA packets from the battery in Fig. 12. When over-sourced, CP_{OS} keeps v_O in Figs. 8 and 12 within ± 28 mV of v_R 's 1 V. Output frequency f_O in this mode is 8–53 Hz (when the load P_{LD} in Fig. 11 is 10–110 μ W). G_{BA} keeps v_O in Fig. 14 within ± 4 mV of v_R . Overall, CP_M keeps v_O in Fig. 14 within +60 and –72 mV of v_R when P_{LD} suddenly changes 5 mW.

C. Power Consumption and Conversion

Losses: Table I details how the system consumes power. PV and mode comparators CP_{PV} and CP_M and the bias block are always on, consuming 540, 630, and 810 nW. L_X 's R_L burns 1.6 μ W when over-sourced and loaded with 35 μ W and burns 101 μ W when battery-assisted and loaded with 5 mW. Switches burn 5.6 μ W when similarly over-sourced and 142 μ W when similarly battery-assisted. Ohmic power is generally higher when battery-assisted because the system transfers more power when loaded to the extent that assistance is needed.

CP_{OS} , CP_O , and CP_B consume 560, 770, and 550 nW when over-sourced. G_{BA} , CP_{BA} , CP_G , and CP_O dissipate 3.6, 6.7, 2.3, and 0.62 μ W when battery-assisted. G_{BA} , CP_{BA} , and CP_G are off when over-sourced and CP_{OS} and CP_B are off when battery-assisted. Battery-assisted components need more power because the system switches faster when battery-assisted, and to react quicker, components need more power.

TABLE I: MEASURED LOSSES

	Over-Sourced: $P_{PV} = 70\text{ }\mu\text{W}, P_{LD} = 35\text{ }\mu\text{W}$	Battery-Assisted: $P_{PV} = 70\text{ }\mu\text{W}, P_{LD} = 5\text{ mW}$		
	Energy/Cycle	Avg. Power	Energy/Cycle	Avg. Power
Bias	12.5 pJ	810 nW ^A	15.6 pJ	810 nW ^A
CP_{PV}	8.3 pJ	540 nW ^A	10.4 pJ	540 nW ^A
CP_M	9.7 pJ	630 nW ^A	12.1 pJ	630 nW ^A
R_L	24 pJ	1.6 μ W	2.0 nJ	101 μ W
Switches	85 pJ	5.6 μ W	2.7 nJ	142 μ W
CP_{OS}	8.6 pJ	560 nW	—	—
CP_O	12 pJ	770 nW	12 pJ	620 nW
CP_B	8.4 pJ	550 nW	—	—
G_{BA}	—	—	69 pJ	3.6 μ W ^A
CP_{BA}	—	—	130 pJ	6.7 μ W ^A
CP_G	—	—	44 pJ	2.3 μ W
Total	169 pJ	11 μ W	5.0 nJ	260 μ W

^ASimulated values.

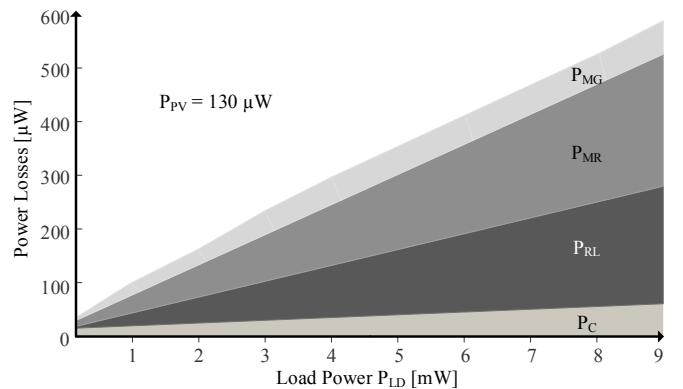


Fig. 16. Measured losses when battery-assisted.

Irrespective of the load P_{LD} , the system transfers PV power P_{PV} when over-sourced. Losses therefore do not change much with P_{LD} in this mode. Battery assistance, on the other hand, increases with P_{LD} . So ohmic losses in L_X 's R_L and the switches P_{RL} and P_{MR} climb with P_{LD} when battery-assisted like Fig. 16 shows. Gate-drive losses P_{MG} also increase with P_{LD} because transistors switch more often when they deliver more battery packets. Controller losses P_C also climb because system components similarly activate more often.

When optimally sized, ohmic and charge losses P_{MR} and P_{MG} in a transistor balance. Here, however, P_{MR} is greater than P_{MG} because P_{MR} also includes the ohmic power that bond wires dissipate. This difference is apparent because bond wires are nearly as resistive as switches in the network.

Efficiency: Power-conversion efficiency η_C is the fraction of input power P_{IN} that a system outputs with P_O . P_{IN} ultimately supplies P_O and losses in the system P_{LOSS} . P_O is therefore the P_{IN} that P_{LOSS} does not dissipate, which is why η_C ultimately hinges on fractional losses P_{LOSS}/P_{IN} :

$$\eta_C = \frac{P_O}{P_{IN}} = \frac{P_O}{P_O + P_{LOSS}} = \frac{P_{IN} - P_{LOSS}}{P_{IN}} = 1 - \frac{P_{LOSS}}{P_{IN}}. \quad (4)$$

The PV controller keeps the size of PV energy packets E_{PV} constant and adjusts their frequency f_{PV} to keep track of PV power P_{PV} . Ohmic, gate-drive, and controller losses P_{RL} and P_{MR} , P_{MG} , and P_C scale with f_{PV} because switches and components engage only when delivering E_{PV} 's. Losses P_{LOSS} therefore scale with the f_{PV} that draws P_{PV} . So at any given load P_{LD} , both P_{IN} and P_{LOSS} scale with P_{PV} . This is why η_C is fairly independent of P_{PV} in Fig. 17.

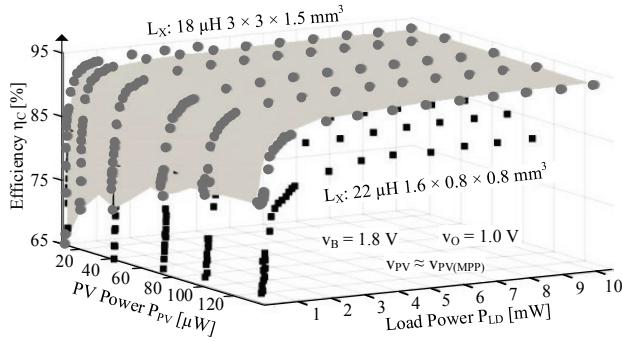


Fig. 17. Measured power-conversion efficiency.

When battery-assisted, v_{PV} and v_B supply P_{IN} and the load sinks P_O . P_{IN} therefore includes PV and battery power P_{PV} and P_B , P_O is the load P_{LD} , P_{IN} supplies P_{LD} and P_{LOSS} , and η_C is

$$\eta_{C(BA)} = \left. \frac{P_O}{P_{IN}} \right|_{BA} = \frac{P_{LD}}{P_{PV} + P_B} = \frac{P_{LD}}{P_{LD} + P_{LOSS}}. \quad (5)$$

Since all losses scale with P_{LD} in Fig. 16, η_C in Fig. 17 is fairly constant across P_{LD} in this mode (when P_{LD} is 0.13–10 mW). η_C is also high at 94.5% because all switches are optimally sized for the energy packets they deliver, system components activate only when needed, and the resistance of the $3 \times 3 \times 1.5\text{-mm}^3$, 18- μH inductor used is only $1\ \Omega$. η_C falls to 87.8% when using a $1.6 \times 0.8 \times 0.8\text{-mm}^3$, 22- μH inductor because, with less volume, resistance is 2× higher.

When over-sourced, v_{PV} supplies P_{LD} and recharges v_B . So

P_{IN} is P_{PV} , P_O includes P_{LD} and P_B , P_O is the P_{PV} that P_{LOSS} does not dissipate, and η_C is

$$\eta_{C(OS)} = \left. \frac{P_O}{P_{IN}} \right|_{OS} = \frac{P_{LD} + P_B}{P_{PV}} = \frac{P_{PV} - P_{LOSS}}{P_{PV}}. \quad (6)$$

Although the system transfers the same P_{PV} that light intensity avails in this mode, P_{LOSS} still changes with P_{LD} . This is because the power that $M_{OP1}-M_{OP2}$ in Fig. 4 steers into v_O and M_{B1} channels into v_B vary with P_{LD} . So as P_{LD} falls, $M_{OP1}-M_{OP2}$ burns less power, but not to the same extent that M_{B1} burns more power. This is why η_C in Fig. 17 falls to 64.3% with the larger L_X and 54.2% with the smaller L_X when P_{LD} is below 130 μW , which is when the system is over-sourced. To improve efficiency in over-sourced mode the supply system switches only when C_{PV} accumulates enough energy to reach v_{MPP} , CP_{OS} remains on only when L_X energizes and, CP_O and CP_B remains on only when L_X drains to output or battery.

V. RELATIVE PERFORMANCE

Table II summarizes the overall performance of this and other light-harvesting power-supply systems in literature. The system here uses a 14-mm 3 22- μH inductor to draw up to 140 μW from a 1-mm 2 PV cell and supply up to 10 mW with 64.3%–94.5% efficiency. With a 1-mm 3 18- μH inductor, efficiency is 54.2%–87.8%.

The switched inductor in [14] draws and supplies the same power, but with a 9.7× larger inductor, 38× larger PV cell, and 11% lower peak efficiency. The one in [24] supplies 20 mW with up to 95% efficiency, but with a 7.0× larger inductor and 740× larger PV cell. [13] uses a 14-mm 3 inductor to draw up to 100 μW , but only supplies up to 1 mW with 8% lower peak efficiency and a 9× larger PV cell. [15] does not report the size of the inductor or PV cell that were used to supply up to 1 μW . The switched capacitor in [12] uses a 0.07-mm 2 PV cell to only draw up to 80 nW and supply 90 nW.

v_{PV} 's and v_O 's capacitors C_{PV} and C_O are normally off-chip because on-chip capacitors are 2.5 nF/mm 3 [18] and off-chip capacitors can be 10 $\mu\text{F}/\text{mm}^3$. This is because the manufacturing process for off-chip capacitors is optimal for capacitors and that of on-chip capacitors is optimal for integrated circuits, not capacitors. Unfortunately, literature does not always report the dimensions of C_{PV} and C_O . But since many off-chip capacitors occupy about 1 mm 3 , assuming C_{PV} and C_O each occupies 1 mm 3 is reasonable.

Literature normally only quotes area for PV cells and silicon dies. This is because height is usually uniform and ultimately dictated by packaging. For the sake of comparison, normalizing cell and die height to 1 mm is reasonable.

When combining the volumes of the transfer inductor, PV cell, and integrated circuit and adding 1 mm 3 for C_{PV} and another 1 mm 3 for C_O , the system prototyped here outputs 561 $\mu\text{W}/\text{mm}^3$ with the larger inductor and 2.08 mW/mm 3 with the smaller one. Whereas, [14], [13], and [24] output 55.2, 39.4, and 23.7 $\mu\text{W}/\text{mm}^3$. So the system here supplies 10× more power per cubic millimeter with 94.5% efficiency and 38× with 87.8% than the best light-harvesting microsystem reported. Effective power density is 3.8× higher in the latter

TABLE II: PERFORMANCE SUMMARY AND COMPARISON WITH THE STATE OF THE ART

	JSSC '15 [14]	TPE '16 [13]	JSSC '16 [24]	JSSC '16 [15]	This Work
PV Cell	$24 \times 1.6 \text{ mm}^2$	$3 \times 3 \times 1 \text{ mm}^3$	$24 \times 31 \text{ mm}^2$		$1 \times 1 \times 1 \text{ mm}^3$
IC Silicon Area	$2.15 \times 2.15 \text{ mm}^2$	$0.6 \times 0.6 \text{ mm}^2$	$0.9 \times 0.9 \text{ mm}^2$	$3 \times 3 \text{ mm}^2$	$0.9 \times 0.9 \text{ mm}^2$
Min. Channel Length	180 nm	180 nm	500 nm	180 nm	180 nm
Transfer Inductor	10 μH	47 μH	4.7 μH		18(22) μH
	136 mm^3	14 mm^3	98 mm^3 ^A		14(1.0) mm^3
		2 Ω	20 m Ω		1(2) Ω
Battery Voltage	3 V	1.8 V	3.3 V	3.0 V	1.8 V
PV Voltage		0.27–0.32 V	1.5–5.5 V	0.14–0.62 V	0.42–0.46 V
PV Capacitor		220 nF	4.7 μF		100 nF
		$1.6 \times 0.8 \times 0.8 \text{ mm}^3$			$1 \times 0.5 \times 0.5 \text{ mm}^3$
PV Ripple	10 mV	30 mV	20 mV		30 mV
PV Power	< 100 μW	< 100 μW	40 μW	50 nW–1 μW	10–140 μW
Output Voltage	1 V, 1.8 V	1 V	1–3.3 V	1 V	1 V
Load Power	1 μW –10 mW	0–1 mW	0–20 mW		0–10 mW
Static Output Ripple	10 mV	10 mV	10 mV	10 mV	10 mV
Output Capacitor	10 μF	2.2 μF	10 μF		10 μF
		$1.6 \times 0.8 \times 0.8 \text{ mm}^3$			$1.6 \times 0.8 \times 0.8 \text{ mm}^3$
Load Dumps		0.10–1.0 mW			0.10–1.0 mW
Dynamic Output Ripple	–?/+? mV	–24/+25 mV	–66/+33 mV		–28/+28 mV
Controller Power	< 400 nW	3–30 μW	2.8 μW	3.2 nW	3–66 μW
Power-Conversion Efficiency	68%–83%	63%–86%	80%–95%	40%–87%	64.3%–94.5% (54.2%–87.8%)
Effective Power Density ^B	55.2 $\mu\text{W}/\text{mm}^3$	39.4 $\mu\text{W}/\text{mm}^3$	23.7 $\mu\text{W}/\text{mm}^3$		561 (2080) $\mu\text{W}/\text{mm}^3$

^AEstimate. ^BMax. Load Power ÷ Total Volume (of inductor, PV cell, IC silicon die, 1 mm^3 for the PV capacitor, and 1 mm^3 for the output capacitor).

because the 22-uH inductor used is 14× smaller than the 18-uH inductor in the former. Effective power density is higher here mostly because of integration: because the PV cell, power stage, and controller are all on chip.

Another key feature of this design that the table cannot describe very well is how efficiency scales with PV and load power P_{PV} and P_{LD} . Like Fig. 17 shows, efficiency here is nearly 94.5% across P_{PV} 's 10–130- μW and P_{LD} 's 0.5–10-mW with the larger inductor and 87.8% with the smaller inductor. Like typical power supplies with small (lossy) inductors, efficiency in [12]–[15] and [24] peaks at one load level and drops with other loads. Efficiency here is constant because C_{POS} , G_{BA} , and C_{PM} regulate v_o in such a way that L_x 's energy packets always carry the same energy. Typical control schemes [13]–[14] regulate v_o in ways that do not achieve this.

VI. CONCLUSION

The light-powered CMOS system presented here draws 10–130 μW from a $1 \times 1\text{-mm}^2$ PV cell and assistance from a battery to supply a 10-mW microsystem and recharge the battery with excess PV power. It outputs 10× more power per cubic millimeter than the best light-harvesting microsystem reported with 94.5% efficiency and 38× with 87.8%. Unlike others whose efficiencies peak at one power level, efficiency here is 94.5% across the cell's 10–130- μW and the load's 0.5–10-mW with a $3 \times 3 \times 1.5\text{-mm}^3$ 18- μH inductor and 87.8% with a $1.6 \times 0.8 \times 0.8\text{-mm}^3$ 22- μH inductor. The key enabling features are integration and energy management. Power

switches are optimally sized, components activate only when needed, and the controller tracks power by adjusting frequency. Delivering more power with less space is vital because the mW's that wireless microsensors can demand can easily overwhelm the power that small onboard sources can sustain.

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